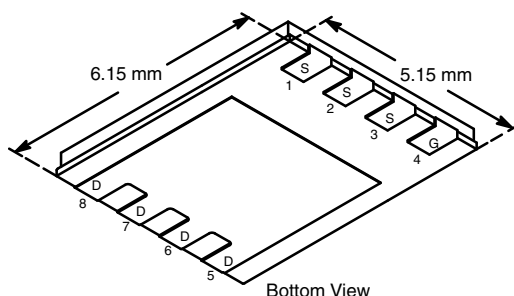


P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω) Max.	I_D (A)	Q_g (Typ.)
- 20	0.0016 at $V_{GS} = -10$ V	- 60 ^d	202.5 nC
	0.0020 at $V_{GS} = -4.5$ V	- 60 ^d	
	0.0032 at $V_{GS} = -2.5$ V	- 60 ^d	

PowerPAK® SO-8



Ordering Information:

Si7157DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

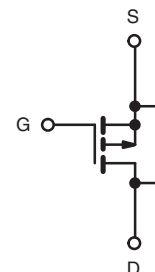
- TrenchFET® Gen III P-Channel Power MOSFET
- 100 % R_g and UIS Tested
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- For Mobile Computing
- Adaptor Switch
- Battery Switch
- Load Switch
- Power Management



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 20	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	A
		$T_C = 70$ °C	
		$T_A = 25$ °C	
		$T_A = 70$ °C	
Pulsed Drain Current ($t_p = 100$ μ s)	I_{DM}	- 300	A
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C	
		$T_A = 25$ °C	
Avalanche Current	I_{AS}	- 35	mJ
Single-Pulse Avalanche Energy	E_{AS}	61.25	
Maximum Power Dissipation	P_D	$T_C = 25$ °C	W
		$T_C = 70$ °C	
		$T_A = 25$ °C	
		$T_A = 70$ °C	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{e, f}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, c}	R_{thJA}	15	20	°C/W
Maximum Junction-to-Case	R_{thJC}	0.9	1.2	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. $t = 10$ s.

c. Maximum under steady state conditions is 54 °C/W.

d. Package limited.

e. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

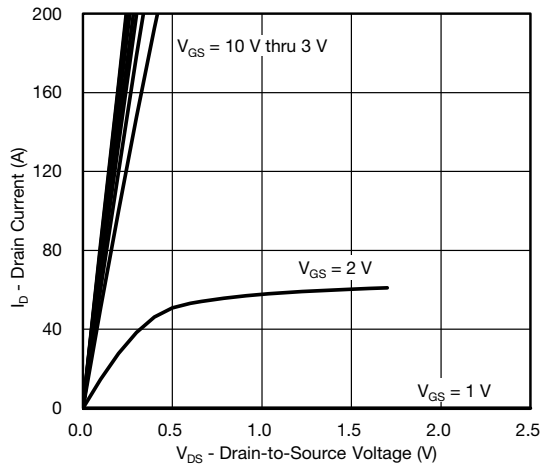
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 20			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 14.5		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			4.1		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 0.5		- 1.4	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 12 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 55 °C			- 5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ - 10 V, V _{GS} = - 10 V	- 40			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 25 A		0.00125	0.00160	Ω
		V _{GS} = - 4.5 V, I _D = - 20 A		0.00155	0.00200	
		V _{GS} = - 2.5 V, I _D = - 15 A		0.00240	0.00320	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 10 V, I _D = - 25 A		120		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = - 10 V, V _{GS} = 0 V, f = 1 MHz		22 000		pF
Output Capacitance	C _{oss}			2470		
Reverse Transfer Capacitance	C _{rss}			2515		
Total Gate Charge	Q _g	V _{DS} = - 10 V, V _{GS} = - 10 V, I _D = - 20 A		415	625	nC
				202.5	305	
Gate-Source Charge	Q _{gs}	V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 20 A		32.5		
Gate-Drain Charge	Q _{gd}			51.5		
Gate Resistance	R _g	f = 1 MHz	0.8	1.5	2.5	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 10 V, R _L = 1 Ω I _D ≅ - 10 A, V _{GEN} = - 10 V, R _g = 1 Ω		20	40	ns
Rise Time	t _r			14	28	
Turn-Off DelayTime	t _{d(off)}			220	400	
Fall Time	t _f			55	110	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 10 V, R _L = 1 Ω I _D ≅ - 10 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		115	200	
Rise Time	t _r			120	220	
Turn-Off DelayTime	t _{d(off)}			230	390	
Fall Time	t _f			75	150	
Drain-Source Body Diode Characteristics						
Continous Source-Drain Diode Current	I _S	T _C = 25 °C			- 60	A
Pulse Diode Forward Current (t _p = 100 μs)	I _{SM}				- 300	
Body Diode Voltage	V _{SD}	I _S = - 5 A, V _{GS} = 0 V		- 0.64	- 1.1	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 10 A, dI/dt = 100 A/μs, T _J = 25 °C		88	140	ns
Body Diode Reverse Recovery Charge	Q _{rr}			120	200	nC
Reverse Recovery Fall Time	t _a			31		ns
Reverse Recovery Rise Time	t _b			57		

Notes:

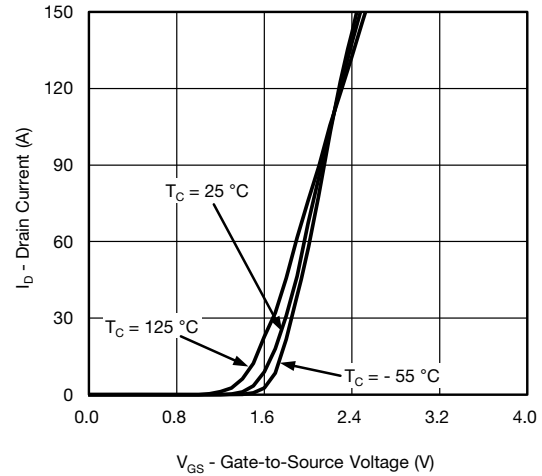
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

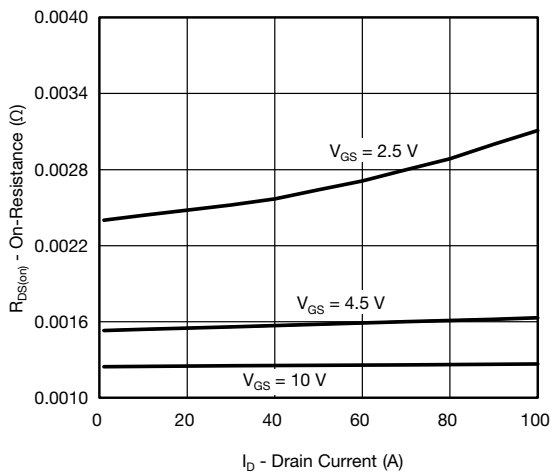
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



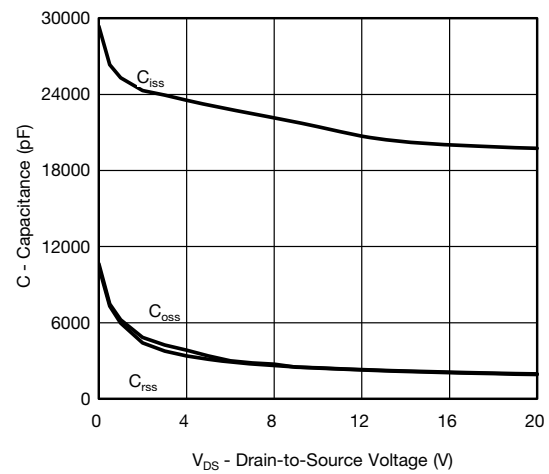
Output Characteristics



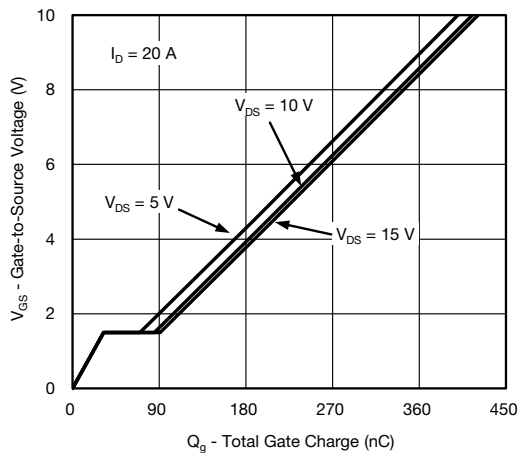
Transfer Characteristics



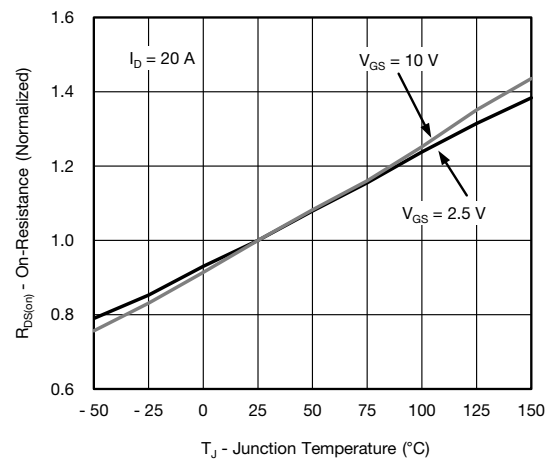
On-Resistance vs. Drain Current



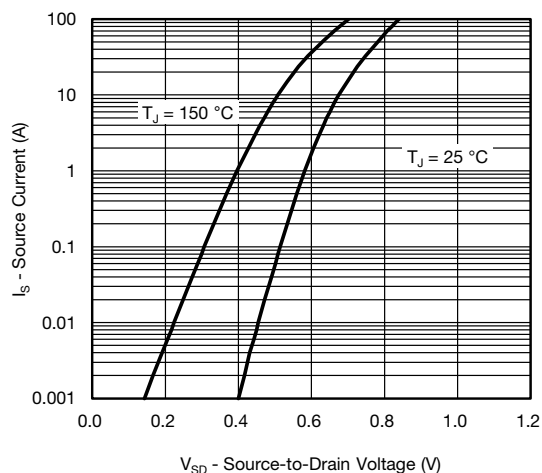
Capacitance



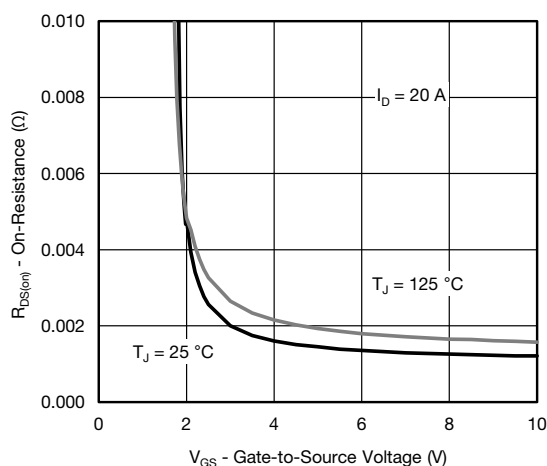
Gate Charge



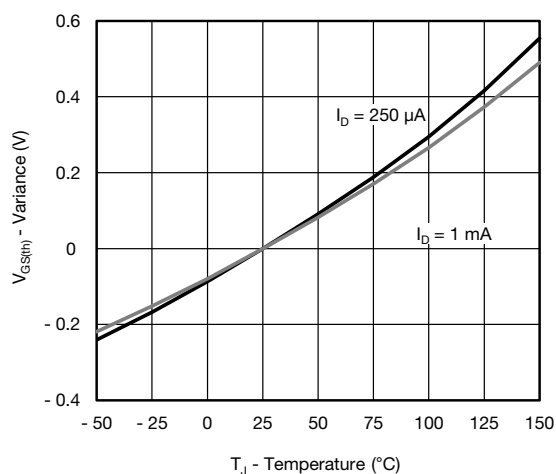
On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

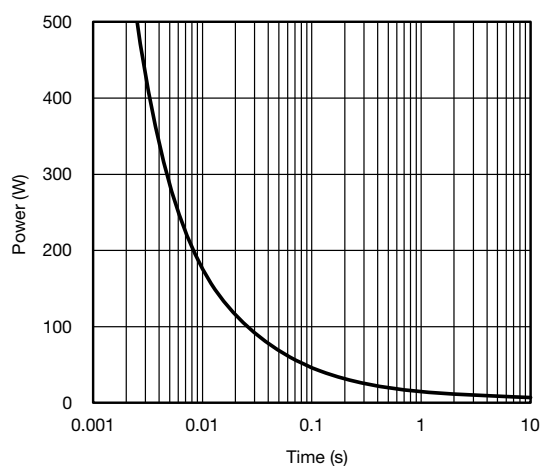
Source-Drain Diode Forward Voltage



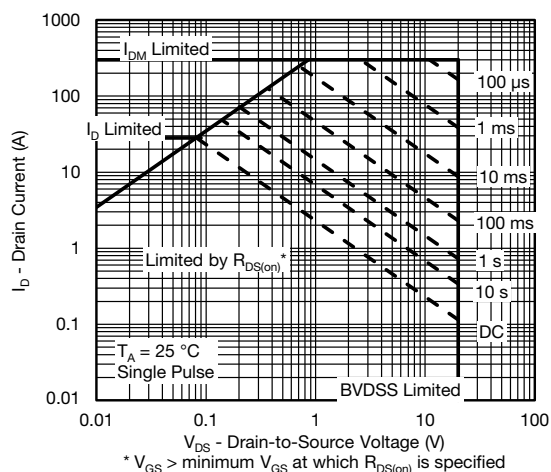
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

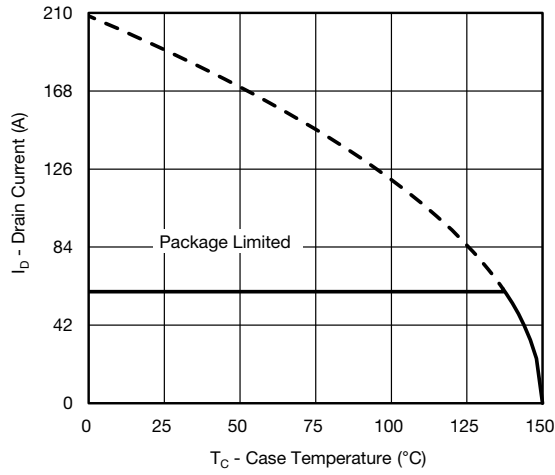


Single Pulse Power, Junction-to-Ambient

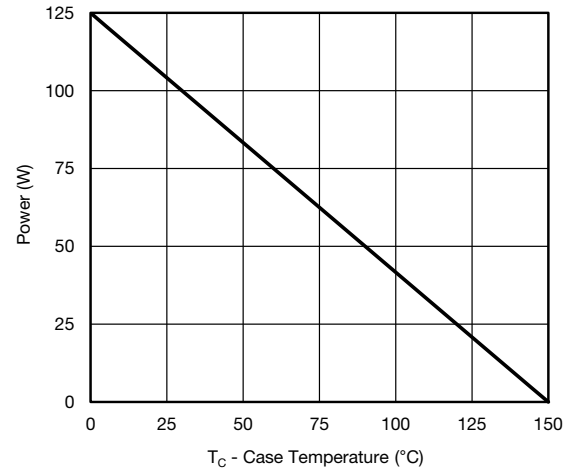


Safe Operating Area

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

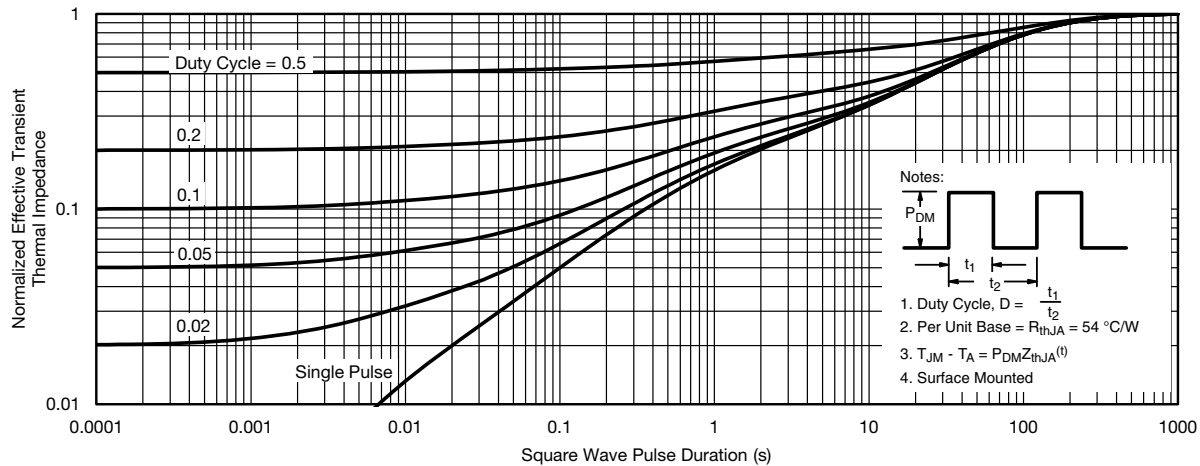
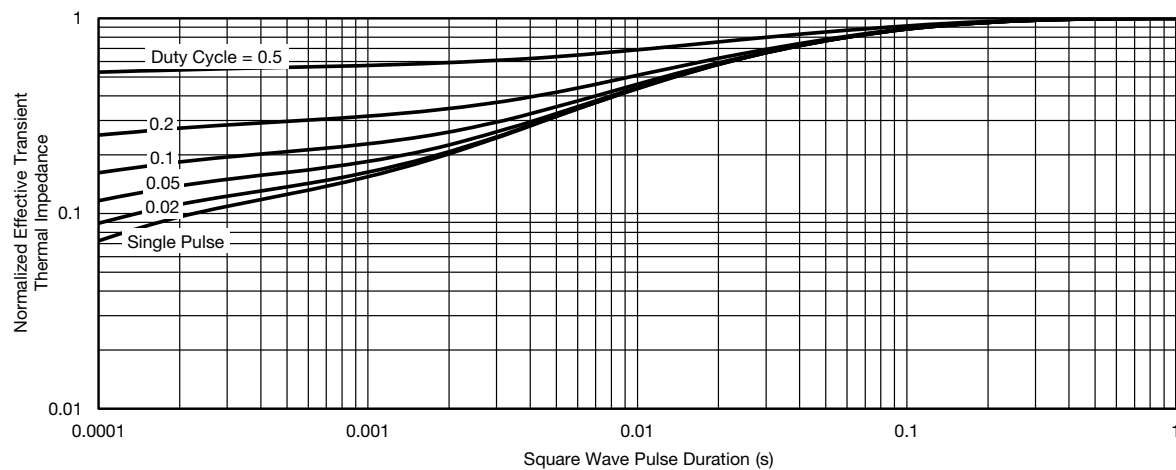


Current Derating*



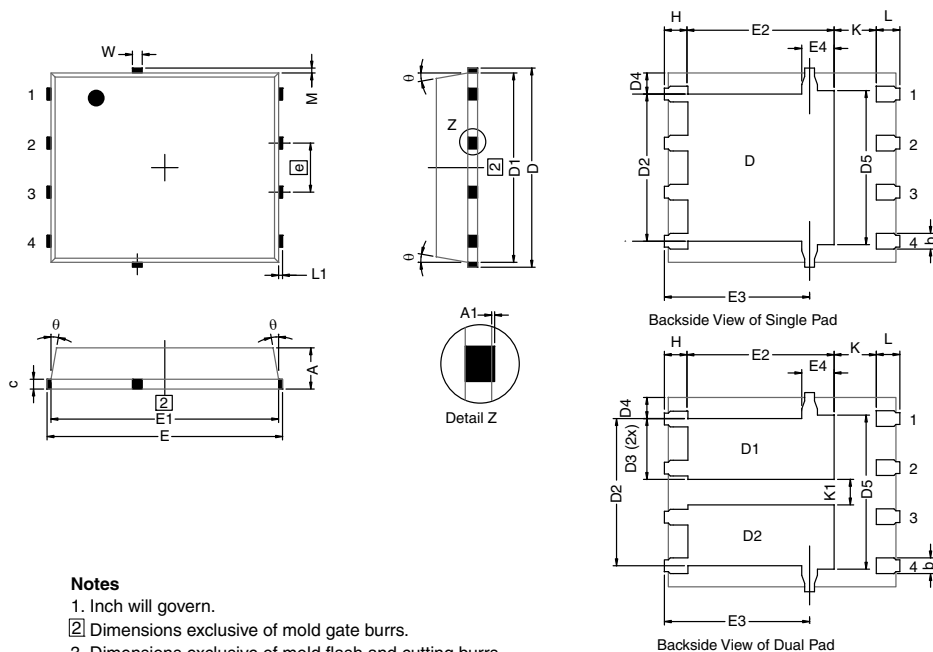
Power, Junction-to-Case

* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Case**

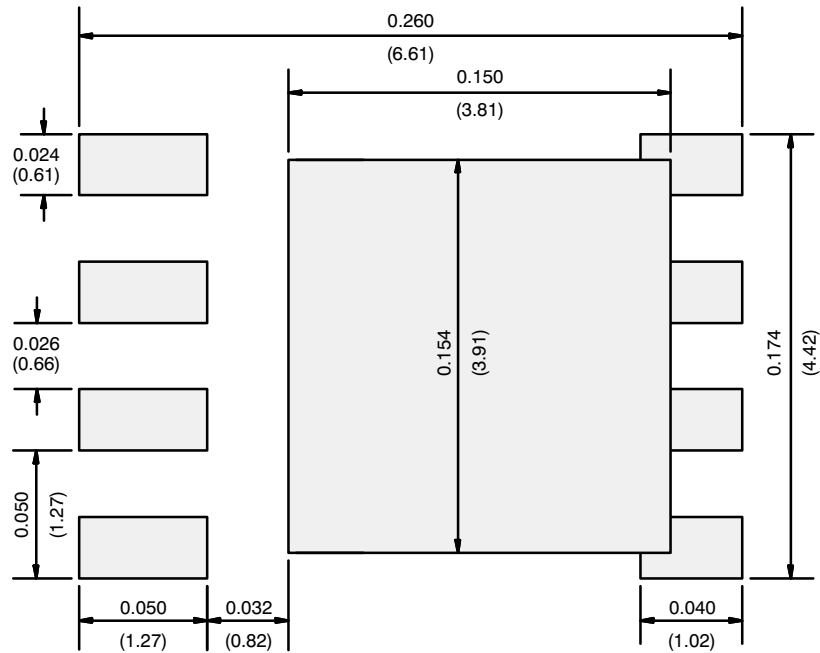
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PowerPAK® SO-8, (Single/Dual)



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.97	1.04	1.12	0.038	0.041	0.044
A1		-	0.05	0	-	0.002
b	0.33	0.41	0.51	0.013	0.016	0.020
c	0.23	0.28	0.33	0.009	0.011	0.013
D	5.05	5.15	5.26	0.199	0.203	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.56	3.76	3.91	0.140	0.148	0.154
D3	1.32	1.50	1.68	0.052	0.059	0.066
D4	0.57 typ.			0.0225 typ.		
D5	3.98 typ.			0.157 typ.		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	5.79	5.89	5.99	0.228	0.232	0.236
E2 (for AL product)	3.30	3.48	3.66	0.130	0.137	0.144
E2 (for other product)	3.48	3.66	3.84	0.137	0.144	0.151
E3	3.68	3.78	3.91	0.145	0.149	0.154
E4 (for AL product)	0.58 typ.			0.023 typ.		
E4 (for other product)	0.75 typ.			0.030 typ.		
e	1.27 BSC			0.050 BSC		
K (for AL product)	1.45 typ.			0.057 typ.		
K (for other product)	1.27 typ.			0.050 typ.		
K1	0.56	-	-	0.022	-	-
H	0.51	0.61	0.71	0.020	0.024	0.028
L	0.51	0.61	0.71	0.020	0.024	0.028
L1	0.06	0.13	0.20	0.002	0.005	0.008
θ	0°	-	12°	0°	-	12°
W	0.15	0.25	0.36	0.006	0.010	0.014
M	0.125 typ.			0.005 typ.		
ECN: C13-0702-Rev. K, 20-May-13						
DWG: 5881						

RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Single



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



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